Erratum: Impact of doping on the density of states and the mobility in organic semiconductors **[Phys. Rev. B 93, 235203 (2016)]**

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In the originally published version an error was made in calculating one of the curves in Fig. 2(c). The correct Fig. 2(c) is shown below.

The corresponding paragraph discussing Fig. 2(c) on page 235203-4 (“The hole mobility ...semiconductor devices.”) as well as the caption remain unchanged.

The y-axis labels of Figs. 1, 2, and 6 displayed $\text{m}^2\text{V s}^{-1}$ instead of $\text{m}^2/\text{V s}$ as the unit.

Moreover, the first and second terms in Eq. (6) as originally shown were improperly normalized. The correct Eq. (6) is

$$g(E) = \left(1 - \frac{4\pi N_d}{3N_i}\right) \frac{g_1(E)}{\int_{-\infty}^0 dE g_1(E)} + \frac{4\pi N_d}{3N_i} \frac{g_2(E)}{\int_{-\infty}^0 dE g_2(E)}, \quad (6a)$$

$$g_1(E) = A \int_{E_1}^0 \frac{dE_c}{E_C^4} \exp\left(\frac{A}{3E_C^3}\right) g_i(E - E_C), \quad (6b)$$

$$g_2(E) = A \int_{-\infty}^{E_1} \frac{dE_c}{E_C^4} \exp\left(\frac{A}{3E_C^3}\right) g_i(E - \Delta E - E_C). \quad (6c)$$

In the actual calculations the correct expressions were used, so neither the results nor the conclusions in the paper are affected.